

DMP3035SFG

30V P-CHANNEL ENHANCEMENT MODE MOSFET PowerDI3333-8

#### **Product Summary**

BV <sub>DSS</sub>	R <sub>DS(ON)</sub> max	I <sub>D</sub> max T <sub>A</sub> = +25°C		
-30V	20mΩ @ V <sub>GS</sub> = -10V	-9.5A		
	29mΩ @ V <sub>GS</sub> = -5V	-8.5A		

## **Description and Applications**

This MOSFET has been designed to minimize the on-state resistance  $(R_{DS(ON)})$  and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

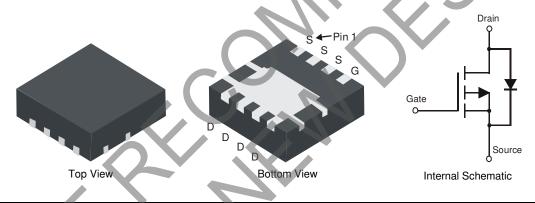
- Backlighting
- Power Management Functions
- DC-DC Converters

#### **Features and Benefits**

- Low R<sub>DS(ON)</sub> Ensures on state losses are minimized
- Small form factor thermally efficient package enables higher density end products
- Occupies just 33% of the board area occupied by SO-8 enabling smaller end product
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

## **Mechanical Data**

- Case: PowerDI<sup>®</sup>3333-8
- Case Material: Molded Plastic, "Green" Molding Compound.
  UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See Diagram Terminals: Finish – Matte Tin Annealed over Copper Leadframe.
- Solderable per MIL-STD-202, Method 208(e3)
- Weight: 0.072 grams (Approximate)



#### Ordering Information (Note 4)

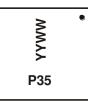
		_		
	Part Number		Case	Packaging
	DMP3035SFG-7		PowerDI3333-8	2000/Tape & Reel
-	DMP3035SFG-13		PowerDI3333-8	3000/Tape & Reel
Notes: 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.				

2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and

- Lead-free. 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and
  - <1000ppm antimony compounds.

4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

## **Marking Information**



P35 = Product Type Marking Code YYWW = Date Code Marking YY = Last Two Digits of Year (ex: 18 = 2018) WW = Week Code (01 to 53)



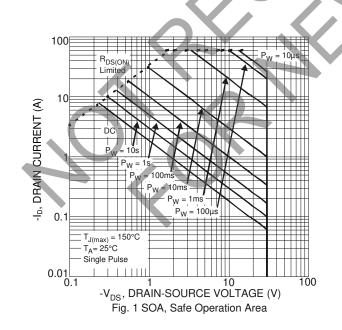
#### **Maximum Ratings** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

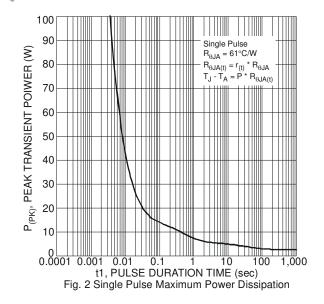
Characteristic	Symbol	Value	Unit		
Drain-Source Voltage	V <sub>DSS</sub>	-30	V		
Gate-Source Voltage		V <sub>GSS</sub>	±25	V	
Continuous Dusis Current (Nate C) V 10V	Steady State	$T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$	ID	-9.5 -6.7	А
Continuous Drain Current (Note 6) $V_{GS} = -10V$	t < 10s	$T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$	ID	-12.5 -10.0	А
Continuous Drain Current (Note C) V EV	Steady State	$T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$	ID	-7.0 -5.5	А
Continuous Drain Current (Note 6) $V_{GS} = -5V$	t < 10s	$T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$	ID	-10.0 -8.0	А
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%	I <sub>DM</sub>	-70	А		
Maximum Continuous Body Diode Forward Current	Is	-3.6	А		

### Thermal Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)		P <sub>D</sub>	0.95	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State		135	°C/W
merinal Resistance, sunction to Ambient (Note 5)	t < 10s	R <sub>0</sub> JA	65	°C/W
Total Power Dissipation (Note 6)		PD	2.3	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	P	55	°C/W
merinal Resistance, sunction to Ambient (Note 6)	t < 10s	R <sub>0JA</sub>	26	°C/W
Thermal Resistance, Junction to Case (Note 6)		R <sub>e</sub> Jc	6.14	°C/W
Operating and Storage Temperature Range		T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

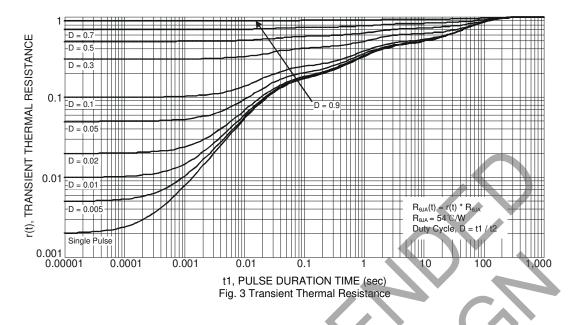
Notes: 5. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout. 6. Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.







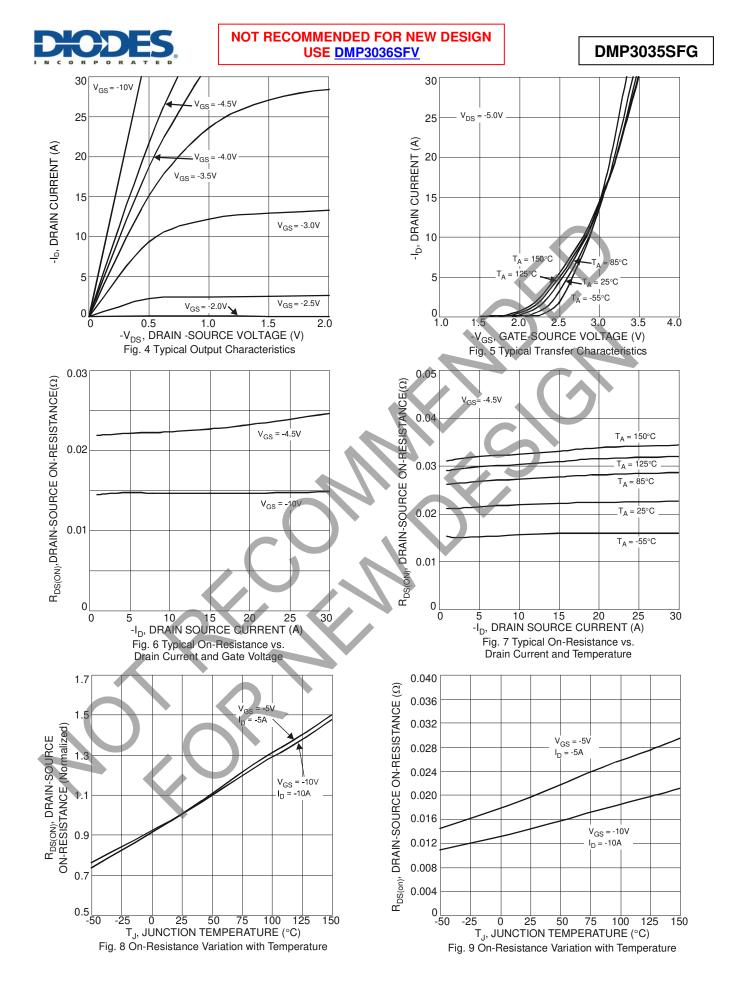
#### NOT RECOMMENDED FOR NEW DESIGN USE <u>DMP3036SFV</u>

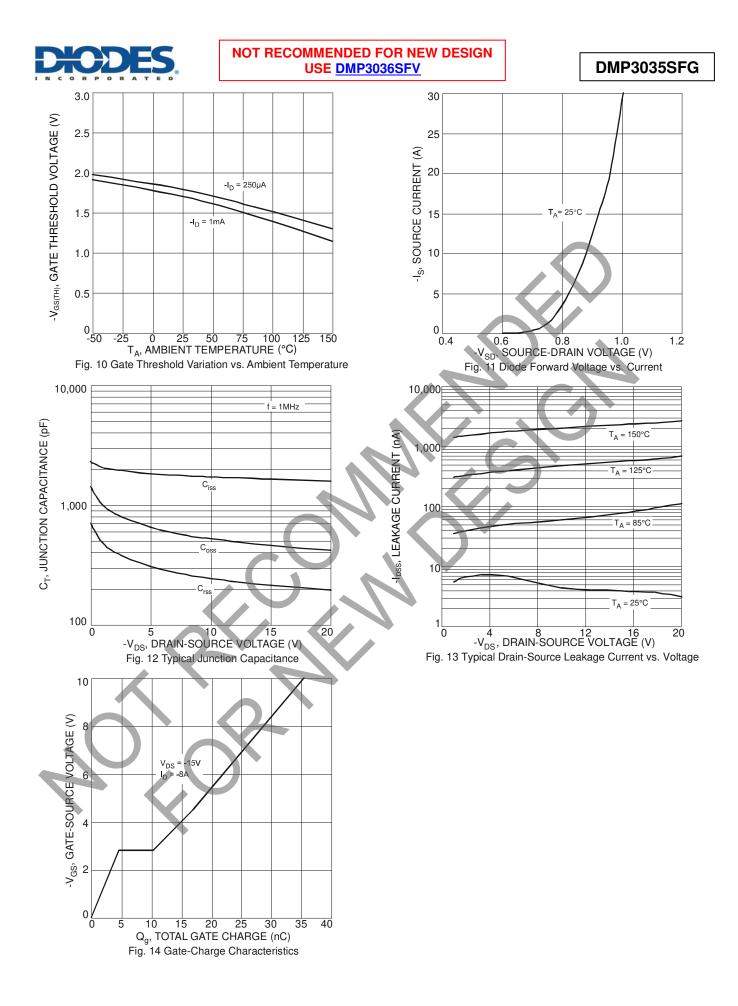


Electrical Characteristics (@T <sub>A</sub> = +25°C, un	less otherwise	specified	1.)				
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)					-		
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	-30	—	—	V	$V_{GS} = 0V, I_D = -250\mu A$	
Zero Gate Voltage Drain Current	IDSS	-		-1.0	μA	$V_{DS} = -30V, V_{GS} = 0V$	
Gate-Source Leakage	lgss	-	_	±100	nA	$V_{GS} = \pm 25V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 7)							
Gate Threshold Voltage	V <sub>GS(TH)</sub>	-1.0	-1.7	-2.5	V	$V_{DS} = V_{GS}, I_D = -250 \mu A$	
Static Drain-Source On-Resistance		—	15	20	mΩ	$V_{GS} = -10V, I_D = -8A$	
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>		21	29	11152	$V_{GS} = -5V, I_D = -5A$	
Forward Transfer Admittance	Y <sub>fs</sub>	-	22	_	S	$V_{DS} = -5V, I_D = -10.0A$	
Diode Forward Voltage	V <sub>SD</sub>	_	-0.74	-1.0	V	$V_{GS} = 0V, I_{S} = -1A$	
DYNAMIC CHARACTERISTICS (Note 8)							
Input Capacitance	C <sub>iss</sub>	—	1633	—	pF		
Output Capacitance	Coss	—	459	—	pF	V <sub>DS</sub> = -15V, V <sub>GS</sub> = 0V, f = 1.0MHz	
Reverse Transfer Capacitance	Crss	_	214	_	pF		
Gate Resistance	Rg	—	6.5	13	Ω	$V_{DS} = 0V, V_{GS} = 0V, f = 1MHz$	
Total Gate Charge V <sub>GS</sub> = -4.5V	Qg	-	17	-	nC		
Total Gate Charge V <sub>GS</sub> = -10V	Qg	-	35.5	-	nC		
Gate-Source Charge	Q <sub>gs</sub>	—	4.6	—	nC	$V_{DS} = -15V, V_{GS} = -10V, I_D = -8A$	
Gate-Drain Charge	Q <sub>gd</sub>	—	5.7	—	nC		
Turn-On Delay Time	t <sub>D(ON)</sub>	—	8.5	—	ns		
Turn-On Rise Time	t <sub>R</sub>	—	14	—	ns	$V_{GEN} = -10V, V_{DD} = -15V,$	
Turn-Off Delay Time	t <sub>D(OFF)</sub>	_	50	_	ns	$R_{GEN} = 3\Omega, I_D = -15A$	
Turn-Off Fall Time	tF	_	25.8	_	ns	7	

# Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Notes: 7. Short duration pulse test used to minimize self-heating effect. 8. Guaranteed by design. Not subject to product testing.



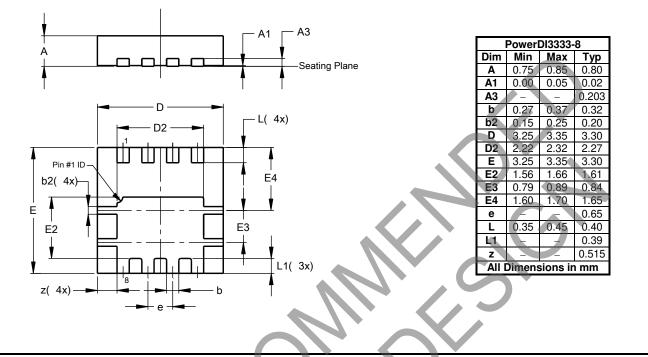




#### **Package Outline Dimensions**

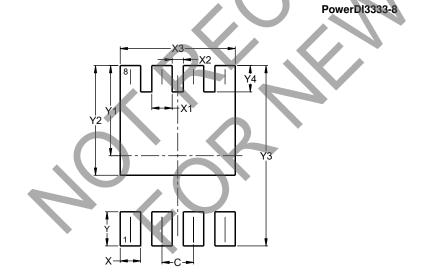
Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI3333-8



# Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.



Dimensions	Value (in mm)
С	0.650
Х	0.420
X1	0.420
X2	0.230
X3	2.370
Y	0.700
Y1	1.850
Y2	2.250
Y3	3.700
Y4	0.540



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